

Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	- 60	
$R_{DS(on)}$ (Ω)	$V_{GS} = - 10$ V	0.50
Q_g (Max.) (nC)	12	
Q_{gs} (nC)	3.8	
Q_{gd} (nC)	5.1	
Configuration	Single	

FEATURES

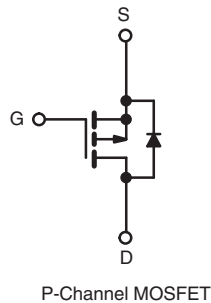
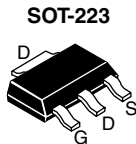
- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- Repetitive Avalanche Rated
- P-Channel
- Fast Switching
- Ease of Paralleling
- Compliant to RoHS Directive 2002/95/EC


 Available
RoHS*
 COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The SOT-223 package is designed for surface-mounting using vapor phase, infrared, or wave soldering techniques. Its unique package design allows for easy automatic pick-and-place as with other SOT or SOIC packages but has the added advantage of improved thermal performance due to an enlarged tab for heatsinking. Power dissipation of greater than 1.25 W is possible in a typical surface mount application.



ORDERING INFORMATION		
Package	SOT-223	SOT-223
Lead (Pb)-free	IRFL9014PbF	IRFL9014TRPbF ^a
	SiHFL9014-E3	SiHFL9014T-E3 ^a
SnPb	IRFL9014	IRFL9014TR ^a
	SiHFL9014	SiHFL9014T ^a

Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS $T_C = 25^\circ\text{C}$, unless otherwise noted				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	- 60	V	
Gate-Source Voltage	V_{GS}	± 20		
Continuous Drain Current	V_{GS} at - 10 V	$T_C = 25^\circ\text{C}$	- 1.8	A
		$T_C = 100^\circ\text{C}$	- 1.1	
Pulsed Drain Current ^a	I_{DM}	- 14	W/ $^\circ\text{C}$	
Linear Derating Factor		0.025		
Linear Derating Factor (PCB Mount) ^e		0.017		
Single Pulse Avalanche Energy ^b	E_{AS}	140	mJ	
Repetitive Avalanche Current ^a	I_{AR}	- 1.8	A	
Repetitive Avalanche Energy ^a	E_{AR}	0.31	mJ	

* Pb containing terminations are not RoHS compliant, exemptions may apply

ABSOLUTE MAXIMUM RATINGS $T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted				
PARAMETER		SYMBOL	LIMIT	UNIT
Maximum Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	3.1	W
Maximum Power Dissipation (PCB Mount) ^e	$T_A = 25\text{ }^\circ\text{C}$		2.0	
Peak Diode Recovery dV/dt^c		dV/dt	- 4.5	V/ns
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature)	for 10 s		300 ^d	

Notes

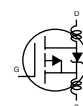
- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. $V_{DD} = - 25\text{ V}$, starting $T_J = 25\text{ }^\circ\text{C}$, $L = 50\text{ mH}$, $R_G = 25\text{ }^\circ\Omega$, $I_{AS} = - 1.8\text{ A}$ (see fig. 12).
- c. $I_{SD} \leq - 6.7\text{ A}$, $dI/dt \leq 90\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DS}$, $T_J \leq 150\text{ }^\circ\text{C}$.
- d. 1.6 mm from case.
- e. When mounted on 1" square PCB (FR-4 or G-10 material).


THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB Mount) ^a	R_{thJA}	-	60	$^\circ\text{C}/\text{W}$
Maximum Junction-to-Case (Drain)	R_{thJC}	-	40	

Note

- a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}$, $I_D = 250\text{ }^\circ\mu\text{A}$	- 60	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$	-	- 0.059	-	$\text{V}/^\circ\text{C}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }^\circ\mu\text{A}$	- 2.0	-	- 4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = - 60\text{ V}$, $V_{GS} = 0\text{ V}$	-	-	- 100	μA
		$V_{DS} = - 48\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 125\text{ }^\circ\text{C}$	-	-	- 500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = - 10\text{ V}$, $I_D = 1.1\text{ A}^b$	-	-	0.50	Ω
Forward Transconductance	g_{fs}	$V_{DS} = - 25\text{ V}$, $I_D = 1.1\text{ A}^b$	1.3	-	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$, $V_{DS} = 25\text{ V}$, $f = 1.0\text{ MHz}$, see fig. 5	-	270	-	pF
Output Capacitance	C_{oss}		-	170	-	
Reverse Transfer Capacitance	C_{riss}		-	31	-	
Total Gate Charge	Q_g	$V_{GS} = - 10\text{ V}$, $I_D = - 6.7\text{ A}$, $V_{DS} = - 48\text{ V}$, see fig. 6 and 13 ^b	-	-	12	nC
Gate-Source Charge	Q_{gs}		-	-	3.8	
Gate-Drain Charge	Q_{gd}		-	-	5.1	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = - 30\text{ V}$, $I_D = - 6.7\text{ A}$, $R_G = 24\text{ }^\circ\Omega$, $R_D = 4.0\text{ }^\circ\Omega$, see fig. 10 ^b	-	11	-	ns
Rise Time	t_r		-	63	-	
Turn-Off Delay Time	$t_{d(off)}$		-	9.6	-	
Fall Time	t_f		-	31	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact	-	4.0	-	nH
Internal Source Inductance	L_S		-	6.0	-	



SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	- 1.8	A
Pulsed Diode Forward Current ^a	I_{SM}		-	-	- 14	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}$, $I_S = -1.8\text{ A}$, $V_{GS} = 0\text{ V}^b$	-	-	- 5.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}$, $I_F = -6.7\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}^b$	-	80	160	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	0.096	0.19	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.

TYPICAL CHARACTERISTICS $25\text{ }^\circ\text{C}$, unless otherwise noted

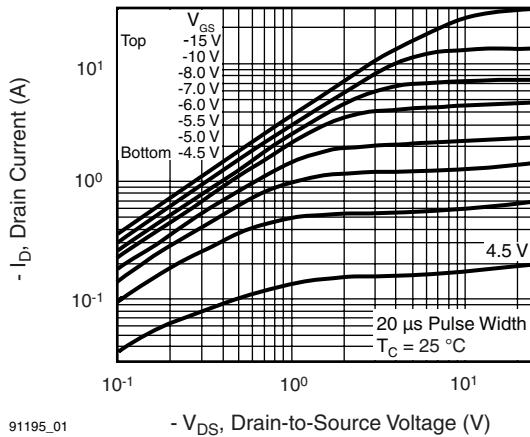


Fig. 1 - Typical Output Characteristics, $T_C = 25\text{ }^\circ\text{C}$

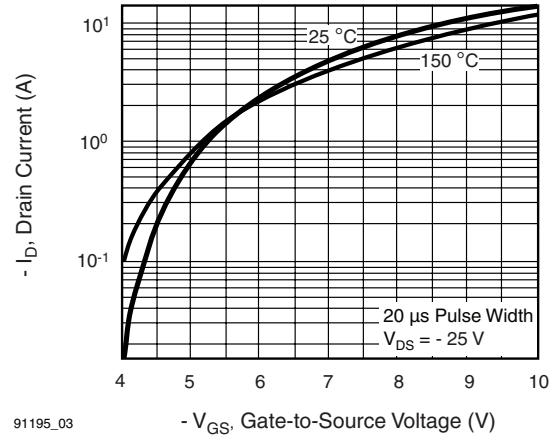


Fig. 3 - Typical Transfer Characteristics

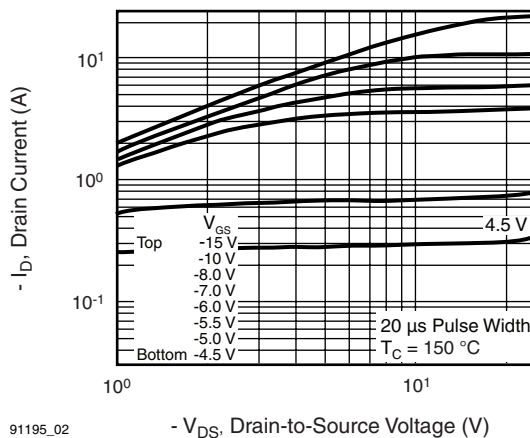


Fig. 2 - Typical Output Characteristics, $T_C = 150\text{ }^\circ\text{C}$

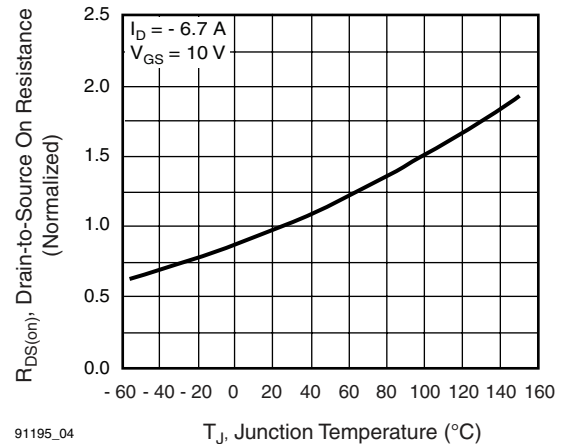
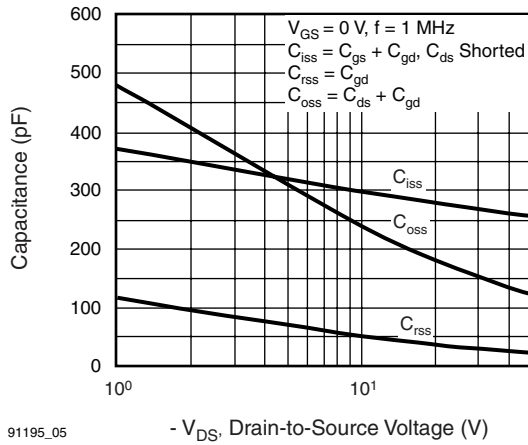
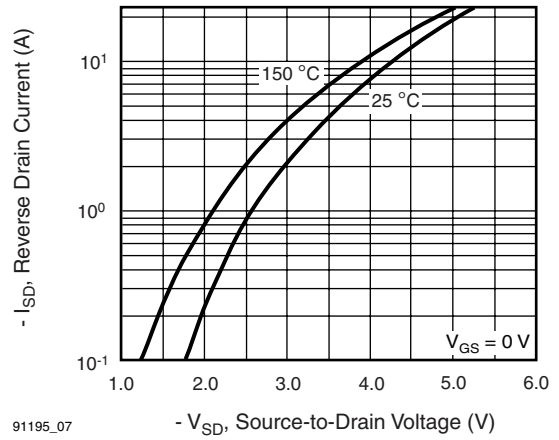


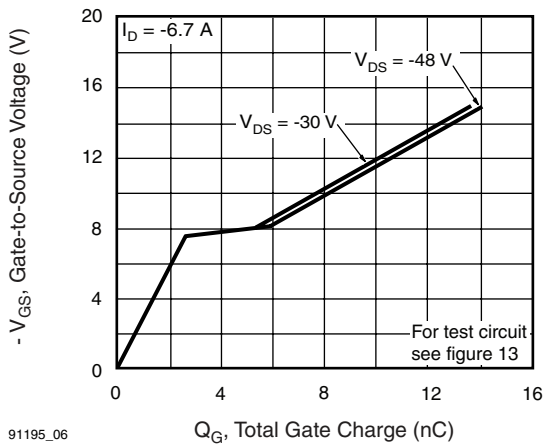
Fig. 4 - Normalized On-Resistance vs. Temperature



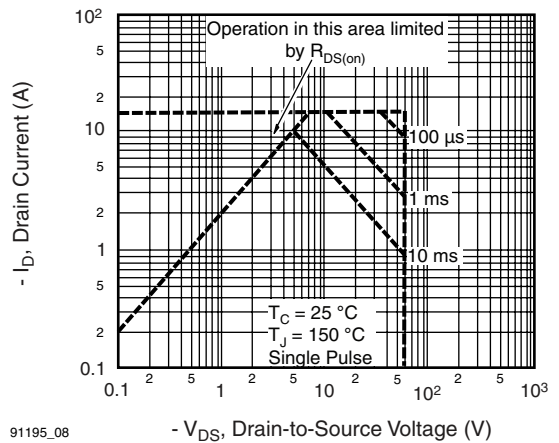
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Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



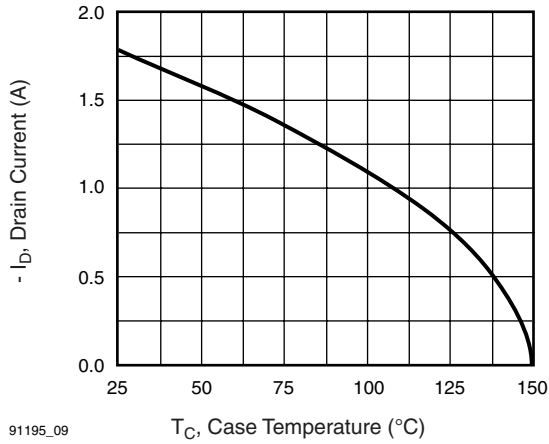
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Fig. 7 - Typical Source-Drain Diode Forward Voltage



91195_06
Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



91195_08
Fig. 8 - Maximum Safe Operating Area



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Fig. 9 - Maximum Drain Current vs. Case Temperature

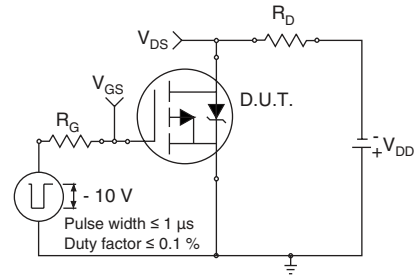


Fig. 10a - Switching Time Test Circuit

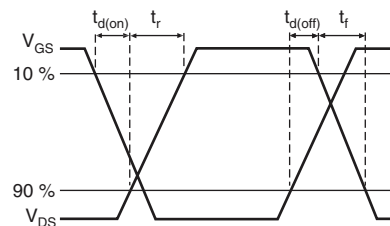
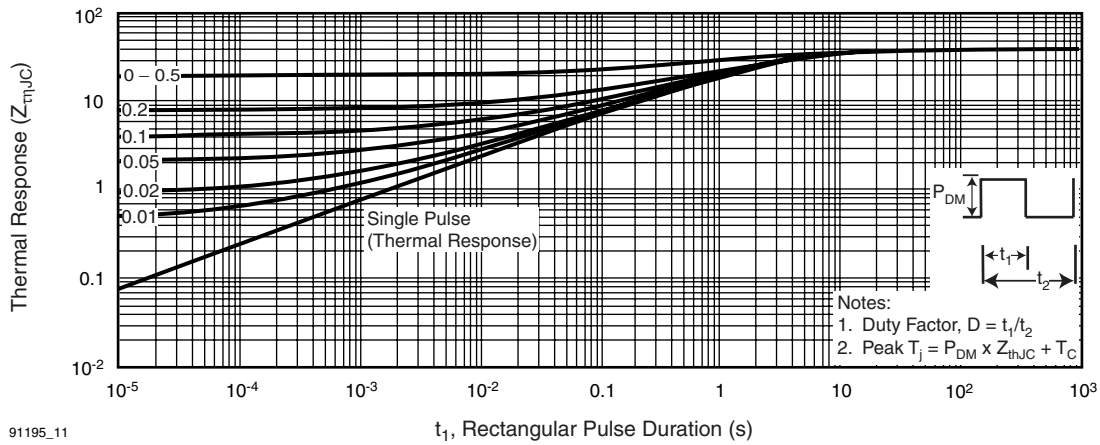


Fig. 10b - Switching Time Waveforms



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Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

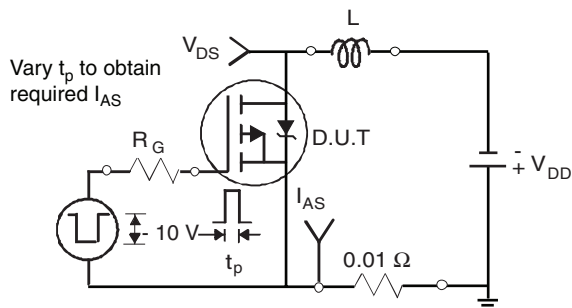


Fig. 12a - Unclamped Inductive Test Circuit

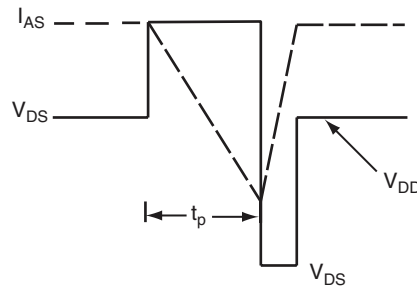


Fig. 12b - Unclamped Inductive Waveforms

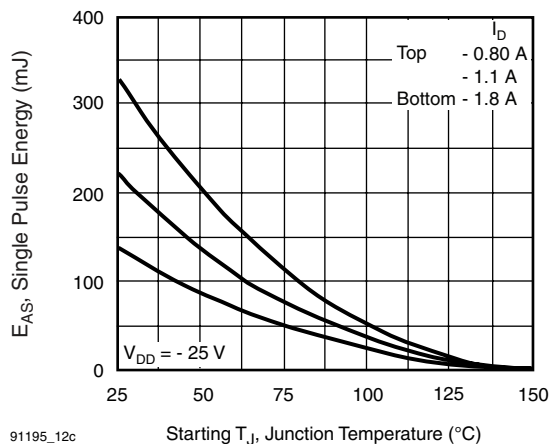


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

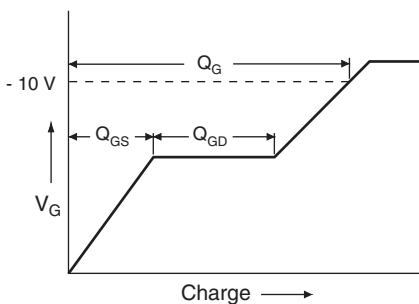


Fig. 13a - Basic Gate Charge Waveform

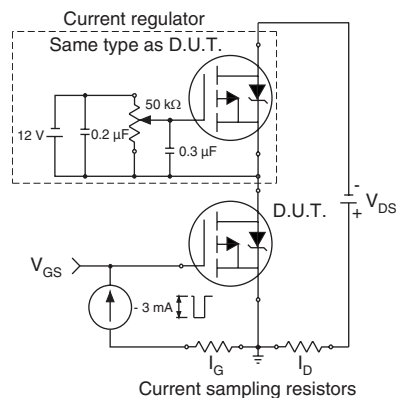
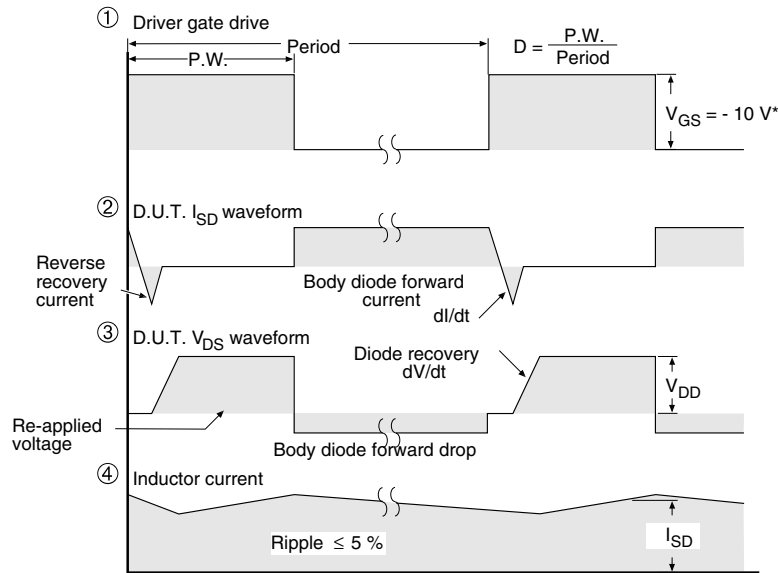
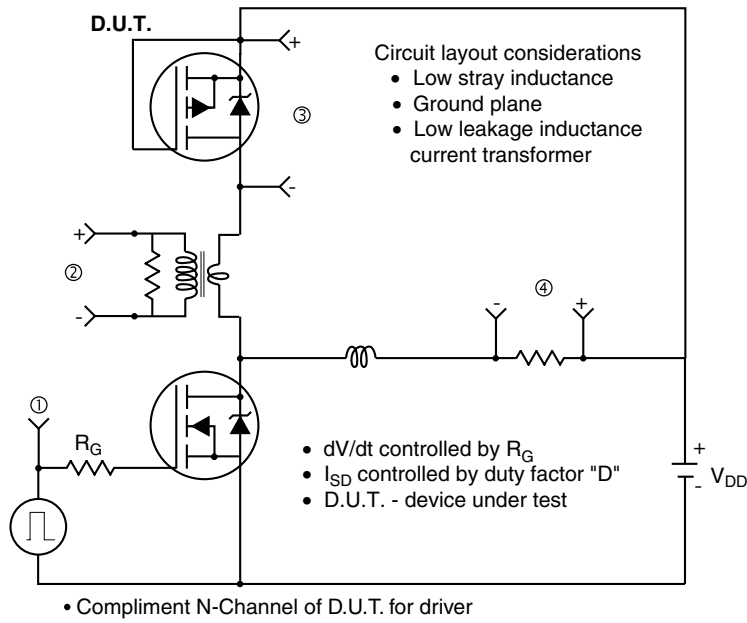


Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



* $V_{GS} = -5 V$ for logic level and $-3 V$ drive devices

Fig.14 - For P-Channel

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